

Radar Pulsed Power Transistor 380 WATTS, 1.2-1.4 GHz, 150us Pulse, 10% DUTY

Production 02 Feb 2012

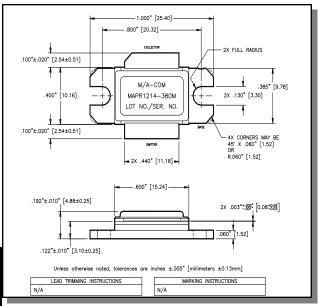
Features

- NPN Silicon Microwave Power Transistors
- Common Base Configuration
- **Broadband Class C Operation**
- High Efficiency Interdigitated Geometry
- **Diffused Emitter Ballasting Resistors**
- Gold Metallization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package
- **RoHS Compliant**

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	88	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	23.9	Α
Power Dissipation @ +25°C	P _{TOT}	700	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: $T_c = 25 \pm 5$ °C (ROOM AMBIENT)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 10mA		BV _{CES}	90	-	٧
Collector-Emitter Leakage Current	V _{CE} = 44V		I _{CES}	-	10	mA
Thermal Resistance	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	0.25	°C/W
Output Power	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	Po	380	-	W
Power Gain	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	G_P	8.8	-	dB
Gain Flatness	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	ΔG_P		1	dB
Droop	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	Droop	-	0.6	dB
Collector Efficiency	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	ης	45	-	%
Input Return Loss	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	2:1	-
Load Mismatch Stability	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

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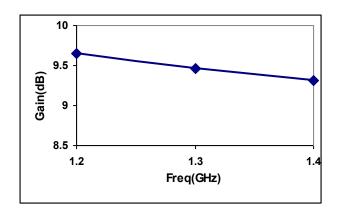
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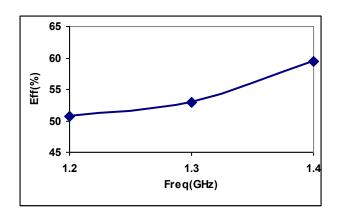
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	ΔGain (dB)	Eff (%)	RL (dB)	Droop (dB)	VSWR-S 1.5:1	VSWR-T 2:01
1.2	50	458.5	9.65		50.75	-23.6	0.15	8	Р
1.3	50	436.8	9.46		52.88	-16.8	-0.02	S	Р
1.4	50	421.3	9.31	0.34	59.52	-15.2	-0.01	S	Р

Gain vs. Frequency



Collector Efficiency vs. Frequency



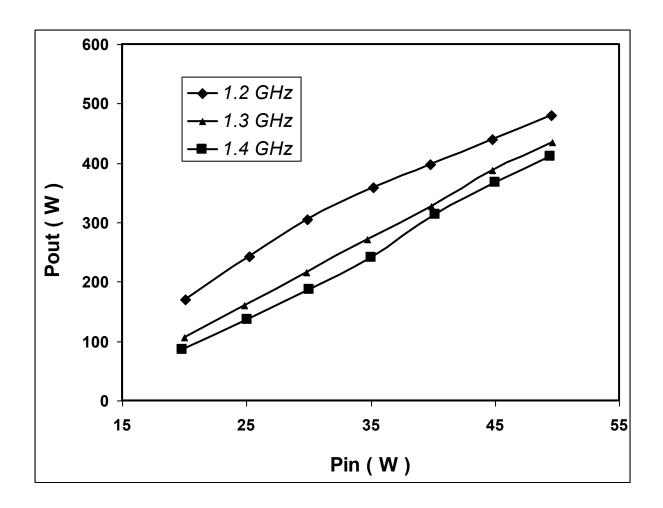
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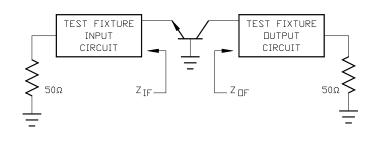
RF Power Transfer Curve (Output Power Vs. Input Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)		
1200	1.3 - j1.89	1.08 - j1.83		
1300	1.43 - j1.28	1.08 - j1.24		
1400	1.51 - j0.73	1.1 - j0.75		

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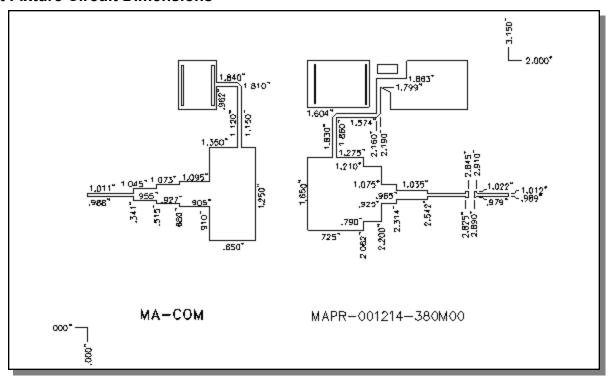
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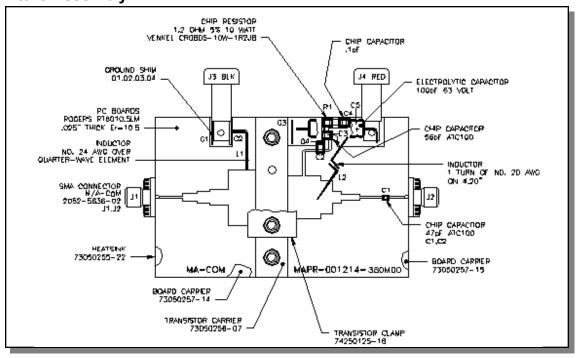
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Test Fixture Circuit Dimensions



Test Fixture Assembly



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